EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	19	(quaternary near layer) near10 (buffer near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:01
L2	2	(quaternary near layer) near10 (buffer near layer) same nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:02
L3	1	10/768944	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:03
L4	16	(quaternary near layer).clm. and (buffer near layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:04
L5	12	(quaternary near layer).clm. and (buffer near layer).clm. and heterostructure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:06
L6	3	(quaternary near layer).clm. and (buffer near layer).clm. and heterostructure and nitride.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:07
L7	3	(quaternary near layer).clm. and (buffer near layer).clm. and nitride.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:07
L8	4	(quaternary near layer).clm. and (buffer near layer).clm. and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:07
L9	16	(quaternary near layer).clm. and (buffer near layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:08

L10	4	(quaternary near layer).clm. and (buffer near layer).clm. and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:08
L11	21	(quaternary near layer) and (buffer near layer).clm. and nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:08
L12	33	(quaternary near layer) and (buffer near layer) same nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:08
L13	3	(quaternary near layer) same (buffer near layer) same nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:09
L14	97	(quaternary near layer) near10 (al or in or ga)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:09
L15	57	(quaternary near layer) near5 (al or in or ga)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:10
L16	3	(quaternary near layer) near2 (comprise or comprises or comprising or include or includes or including) near2 (al or in or ga)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:11
L17	42	(quaternary near layer) near2 (comprise or comprises or comprising or include or includes or including)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:15
L18	98	(nitride near10 heterostructure) and ((insulating or dielectric) near2 substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:16
L19	40	(nitride near10 heterostructure) and ((insulating or dielectric) near2 substrate) and ((buffer or barrier) adj layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:17

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L20	0	(nitride near10 heterostructure) and ((insulating or dielectric) near2 substrate) and ((buffer or barrier) adj layer).clm. and (in near2 al near2 ga near2 n).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:18
L21	13	(nitride near10 heterostructure) and ((insulating or dielectric) near2 substrate) and ((buffer or barrier) adj layer).clm. and quaternary	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:19
L22	5	(nitride near10 heterostructure) and ((insulating or dielectric) near2 substrate) and ((buffer or barrier) adj layer).clm. and (AlGaInP)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:20
L23	7	(nitride near10 heterostructure) and ((insulating or dielectric) near2 substrate) and ((buffer or barrier) adj layer).clm. and (AlGaInN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:21
L24	0	(nitride near10 heterostructure) and ((insulating or dielectric) near2 substrate) and ((buffer or barrier) adj layer).clm. and (AlGaInN).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:20
L25	40	(nitride near10 heterostructure) and ((insulating or dielectric) near2 substrate) and ((buffer or barrier) adj layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:25
L26	29	(nitride near10 heterostructure) and ((insulating or dielectric) near2 substrate) and quaternary	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:33
L27	5	"6563141"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/30 22:33